## UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,847,535 B2

Page 1 of 2

APPLICATION NO.: 10/077784

DATED

: January 25, 2005

INVENTOR(S)

: Terry L. Gilton et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

### Title page,

Item [56], References Cited, OTHER PUBLICATIONS,

"Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag2Se single cyrstal near the phase transition, Inorganic Materials 23 (1987) 137-139." should read:

-- Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag<sub>2</sub>Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139. --.

"Elliot, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034."; should read:

-- Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034. --.

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relation in fats ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985." should read:

-- Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relation in fast ion and mixed conductors, Proceedings of the 6th Risco International symposium, Sep. 9-13, 1985. --; and

"Welrauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett, 16 (1970) 72-73." should read:

-- Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73. --.

#### Column 4.

Line 47, "At shown" should read -- As shown --;

Line 49, "card illustrated" should read -- card 200 inserted within the housing 302 define the location of the memory cells 202 illustrated --; and

### Column 5.

Line 45, "which is has" should read -- which has --; and

# UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO. : 6,847,535 B2 APPLICATION NO.: 10/077784

: January 25, 2005

Page 2 of 2

DATED INVENTOR(S)

: Terry L. Gilton et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

#### Column 9,

Line 4, "at cast" should read -- at least --; and Line 6, "at lest" should read -- at least --.

Signed and Sealed this

Twentieth Day of June, 2006

JON W. DUDAS Director of the United States Patent and Trademark Office